

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((silicon near substrate) (semiconductor near substrate) wafer) with (depression recess aperture aperture) with (contuctive near1 (hole via)) with (insulat \$3 dielectric) with ((flush\$3 coplanar) with surface)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:03
L2	0	((silicon near substrate) (semiconductor near substrate) wafer) same (depression recess aperture aperture) same (contuctive near1 (hole via)) same (insulat\$3 dielectric) same ((flush\$3 coplanar) with surface)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:04
L3	0	((silicon near substrate) (semiconductor near substrate) wafer) and (depression recess aperture aperture) and (contuctive near1 (hole via)) and (insulat \$3 dielectric) and ((flush\$3 coplanar) with surface)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:04

L5	4	((silicon near substrate) (semiconductor near substrate) wafer) with (((interconnect\$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) with (insulat\$3 dielectric)). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:09
L6	5	((silicon near substrate) (semiconductor near substrate) wafer) same (((interconnect \$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) same (insulat\$3 dielectric)). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:10
L7	14	((silicon near substrate) (semiconductor near substrate) wafer) and (((interconnect\$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) and (insulat\$3 dielectric)). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:10
L8	10	7 not 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:10

L9	243	"257"/\$.ccls. and ((silicon near substrate) (semiconductor near substrate) wafer) and (((interconnect\$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) and (insulat\$3 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:12
L10	137	"438"/\$.ccls. and ((silicon near substrate) (semiconductor near substrate) wafer) and (((interconnect\$3 conductive) near1 (hole via)) with ("same" similar) with (wafer silicon semiconductor)) and (insulat\$3 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:13
L11	249	9 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:13
L12	173	11 and (conductive near1 (hole vias))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/13 10:13

4/ 13/ 2009 10:15:00 AM

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